

A cross-sectional diagram of a semiconductor device during ion implantation. The substrate is labeled 1. A thin layer 6 is on the surface. A rectangular block 14 is positioned above the surface. Arrows labeled "Ion implantation" point down towards the surface. A layer 12 is shown beneath the surface, and a layer 15 is shown beneath the block 14. The device is flanked by two hatched regions labeled 2.

FIG. 2A

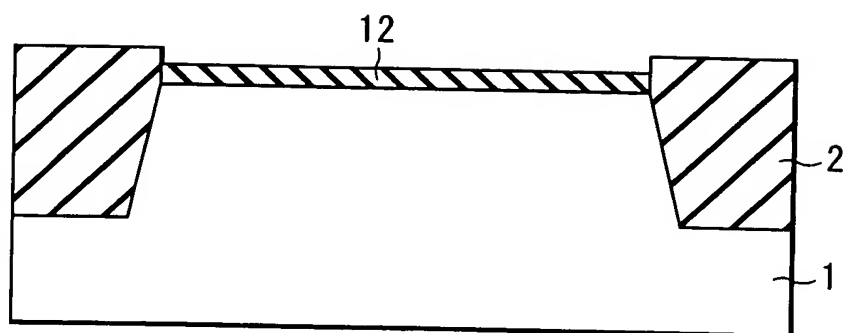


FIG. 2B

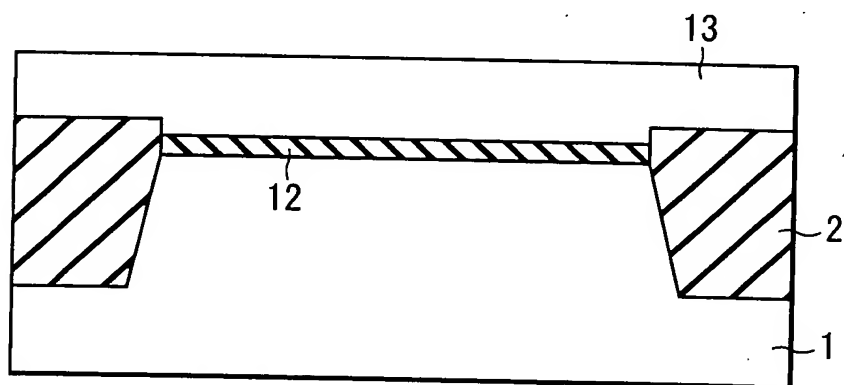


FIG. 2C

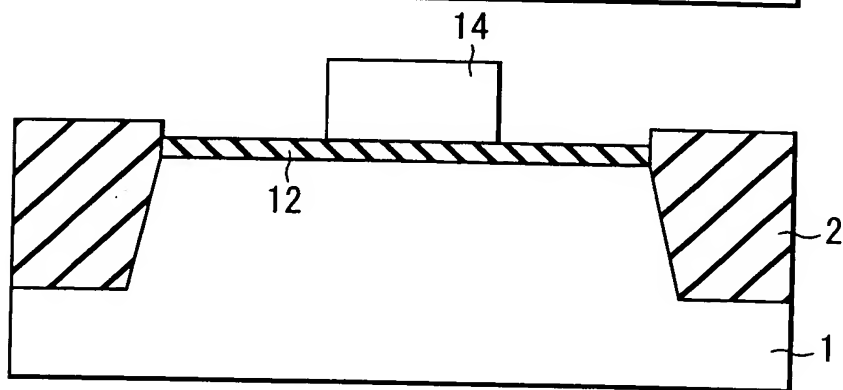
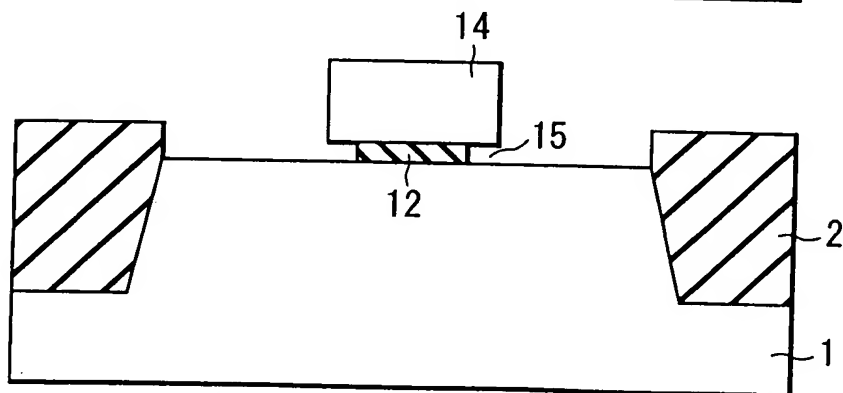


FIG. 2D



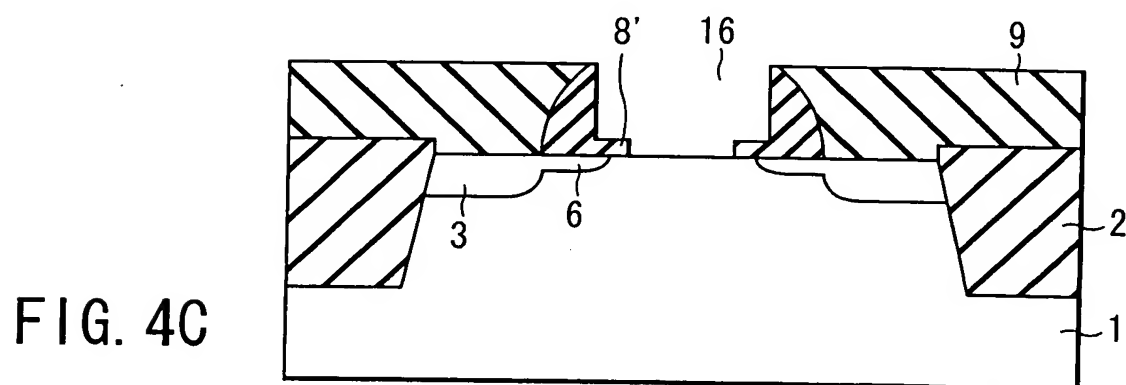
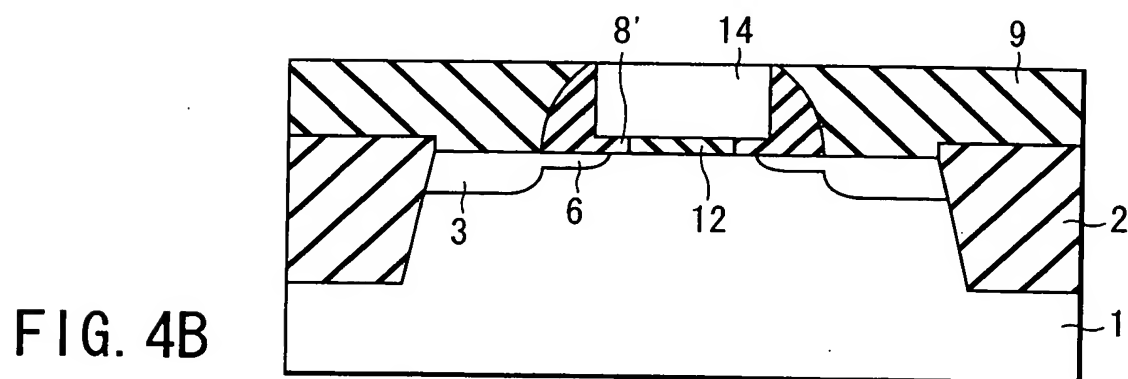
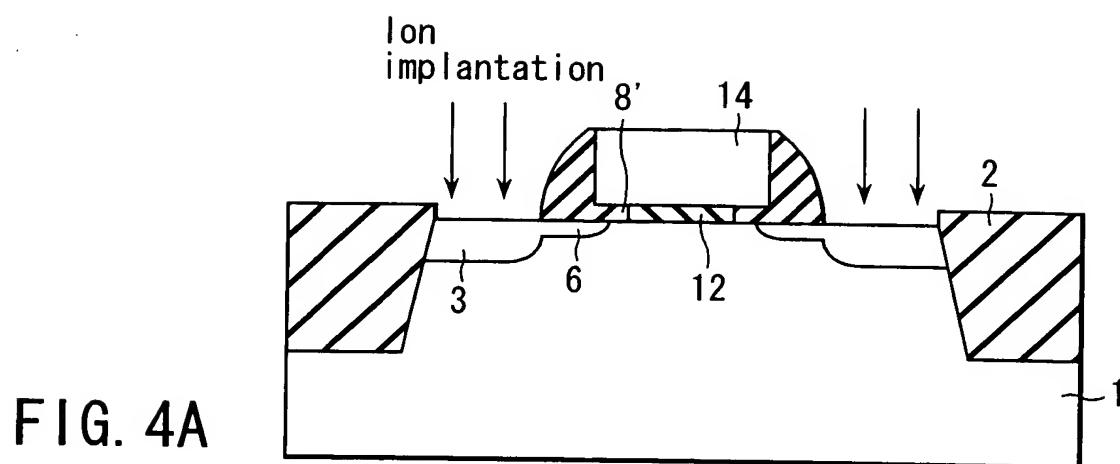


FIG. 5A

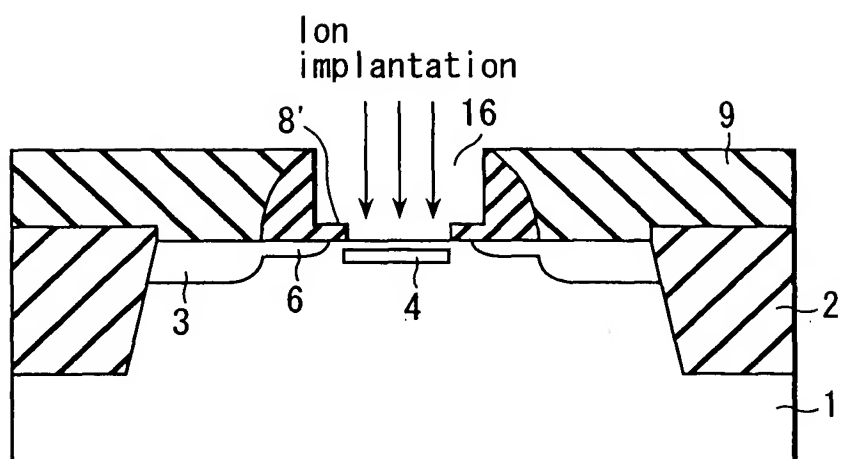


FIG. 5B

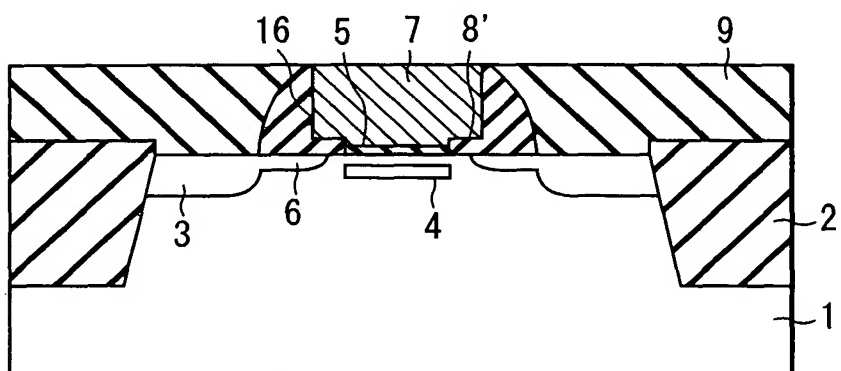


FIG. 6

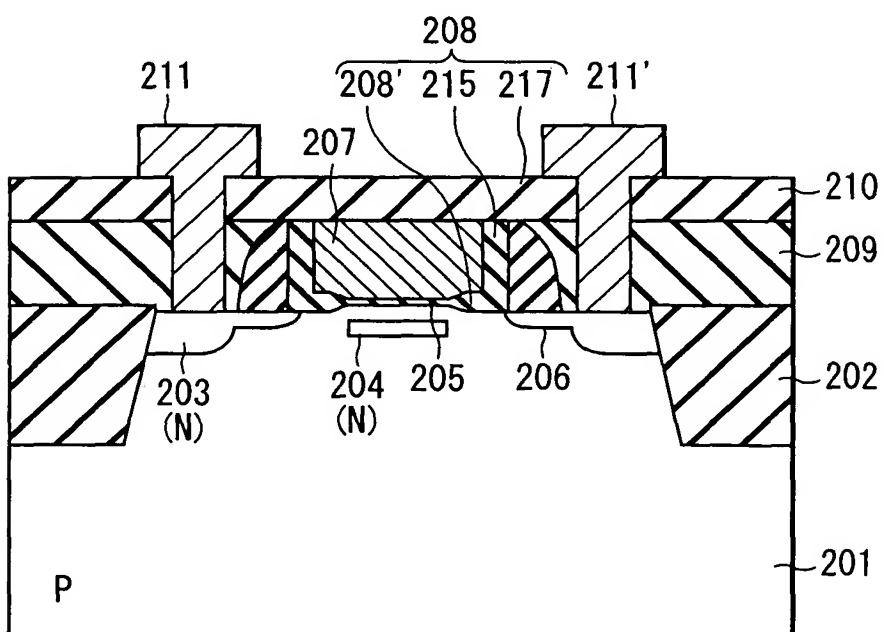


FIG. 7A

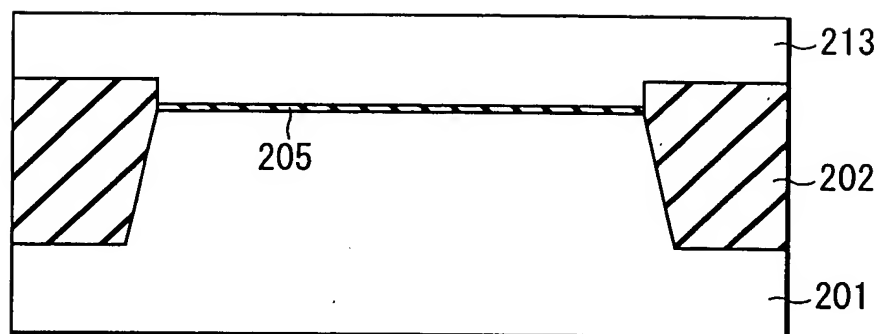


FIG. 7B

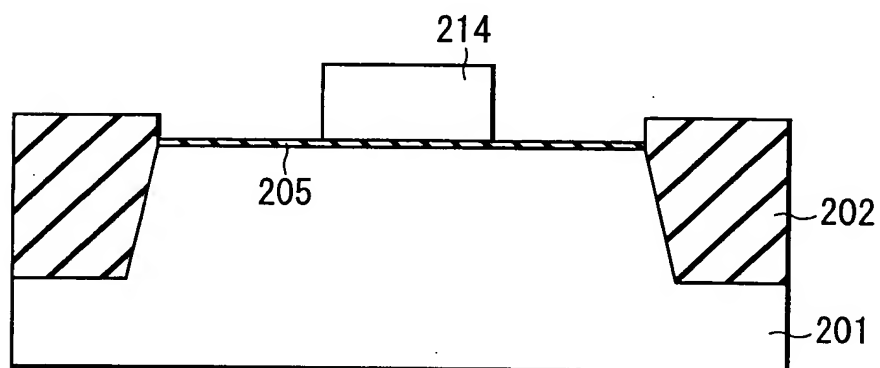


FIG. 7C

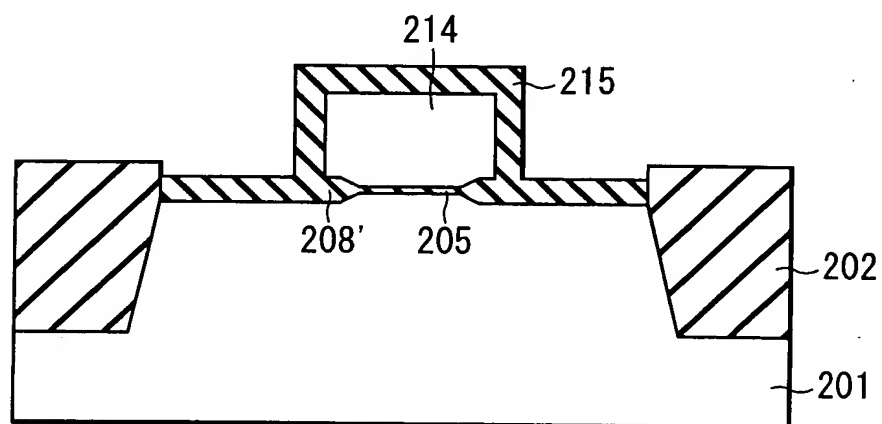


FIG. 8A

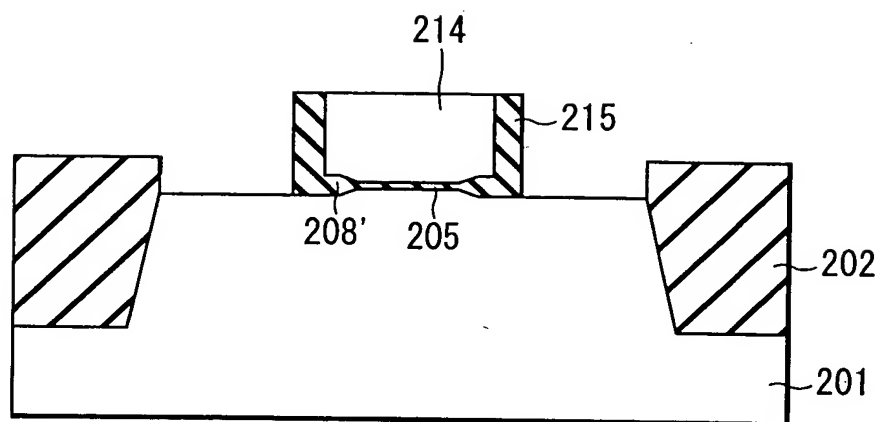


FIG. 8B

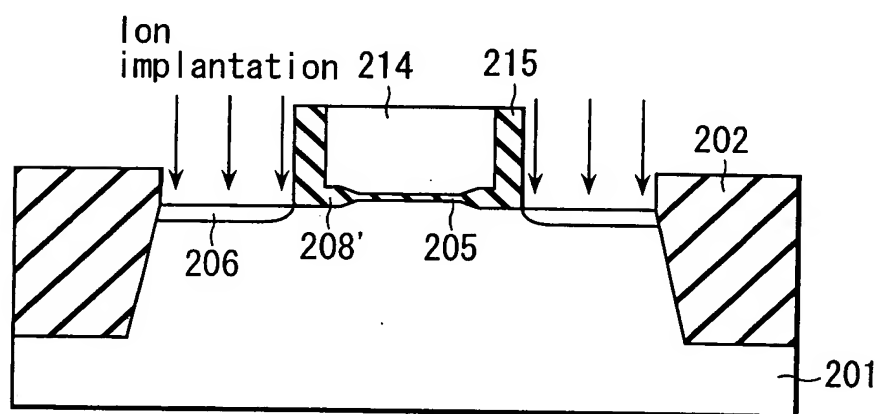


FIG. 8C

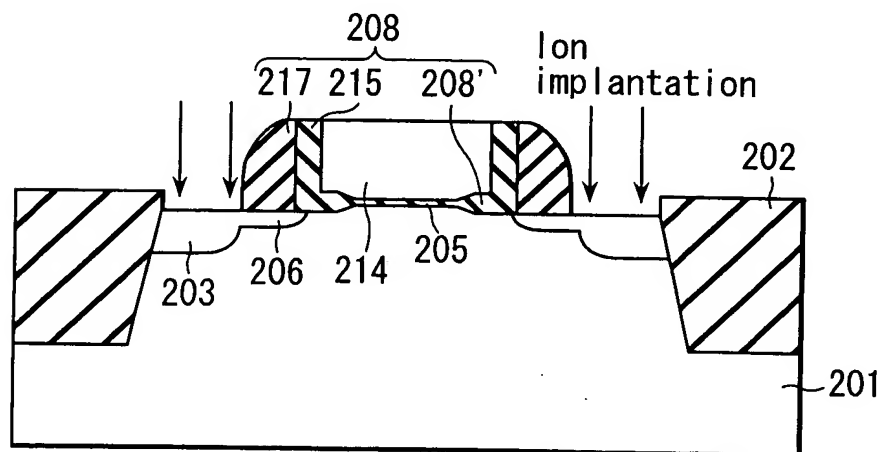


FIG. 9A

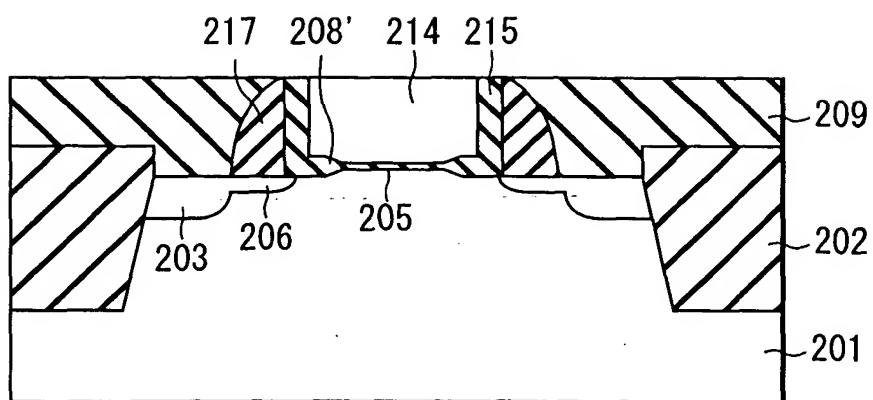


FIG. 9B

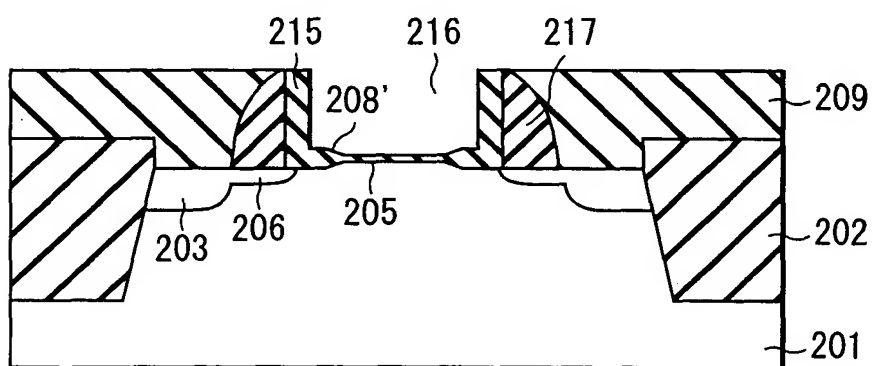


FIG. 10A

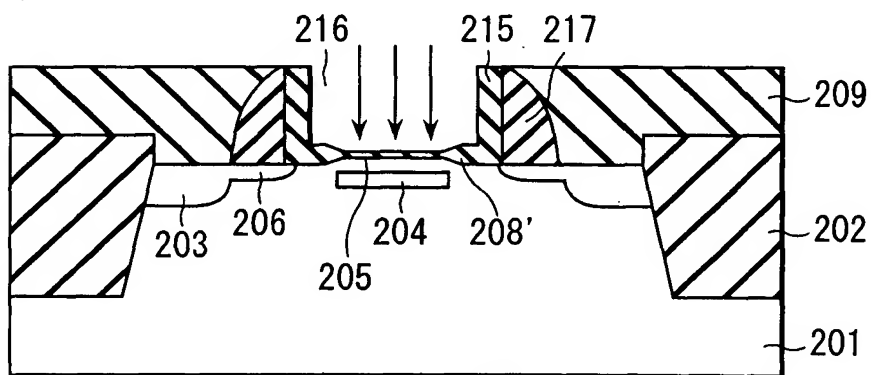


FIG. 10B

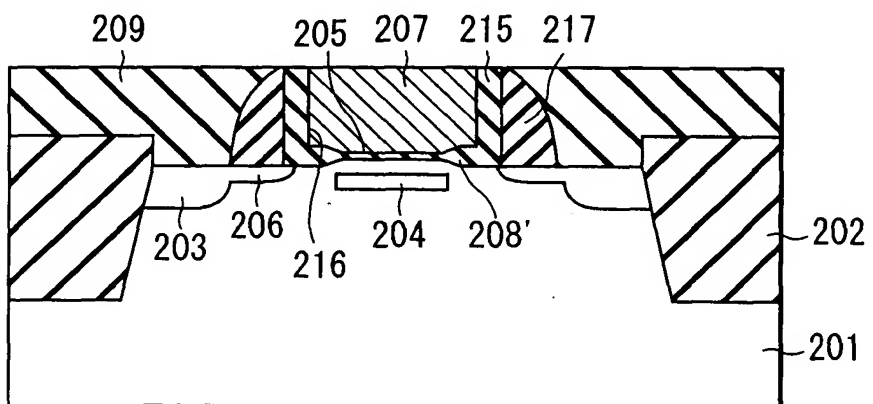


FIG. 11A  
PRIOR ART

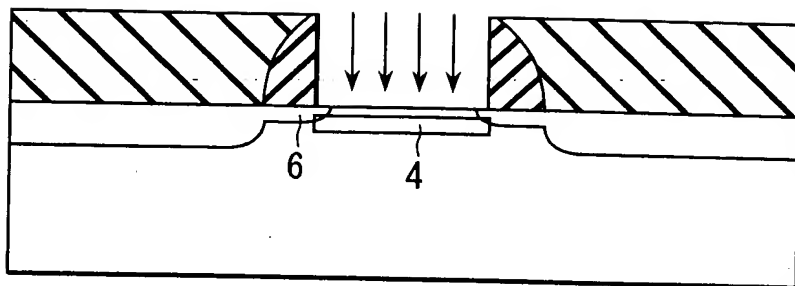


FIG. 11B

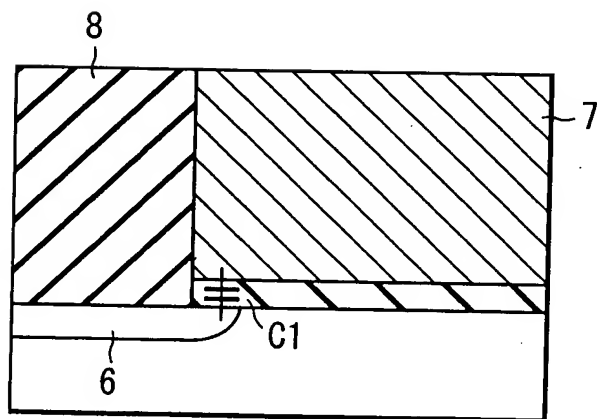
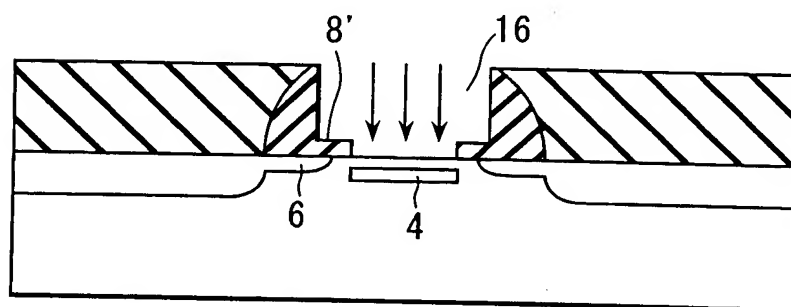


FIG. 12A  
PRIOR ART

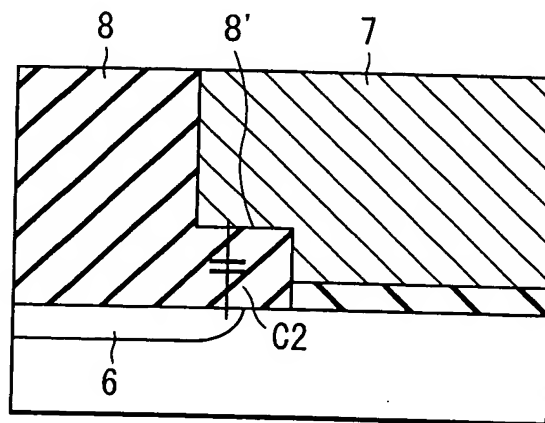


FIG. 12B



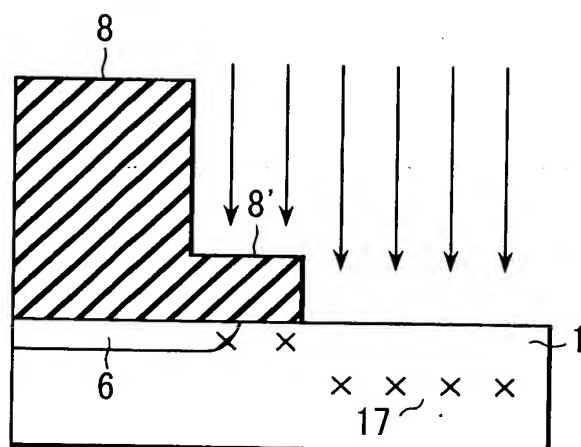


FIG. 13A

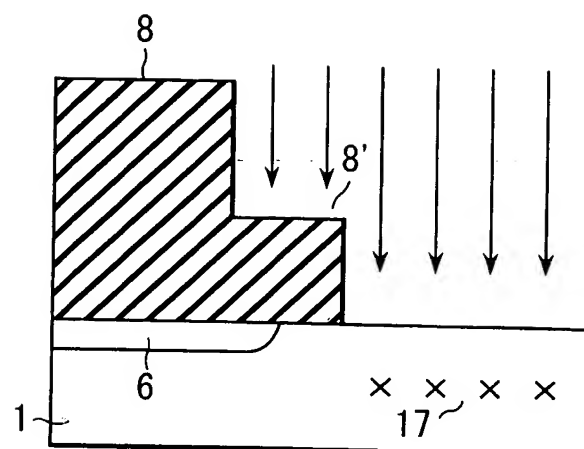


FIG. 13B

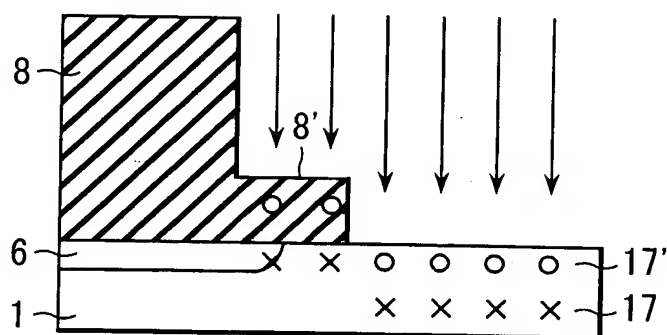


FIG. 13C

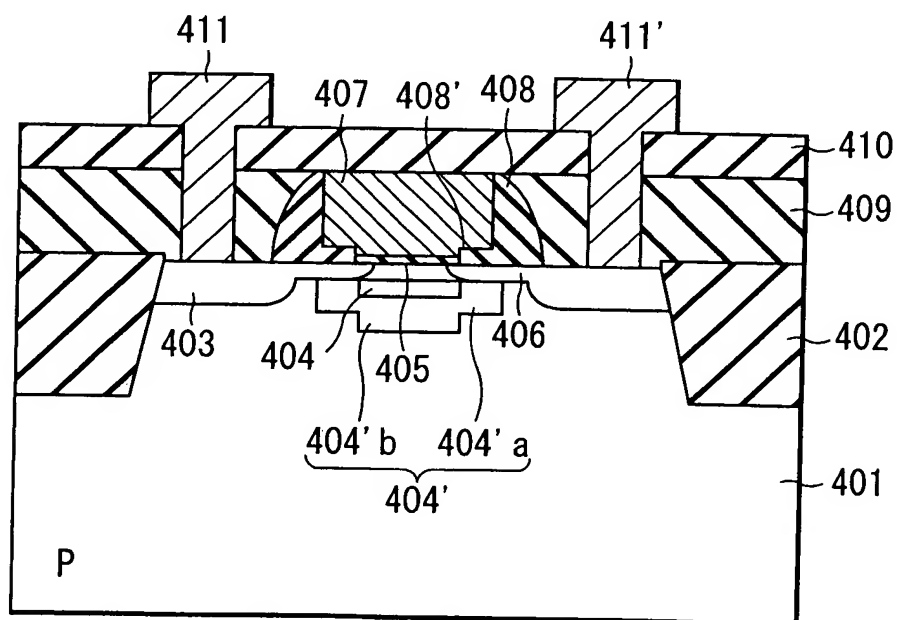


FIG. 14

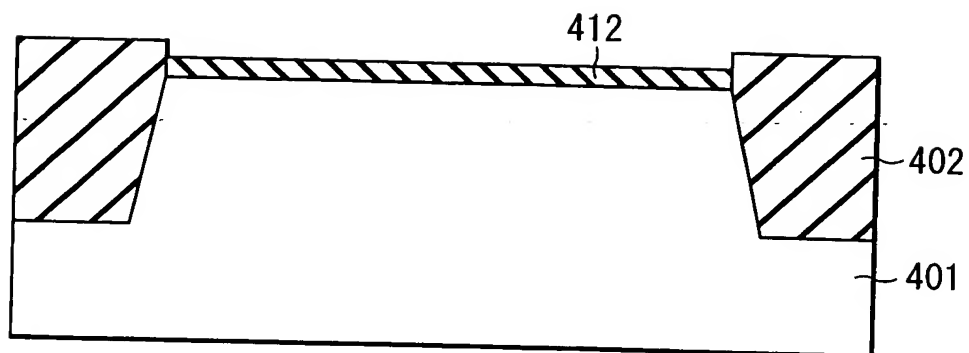


FIG. 15A

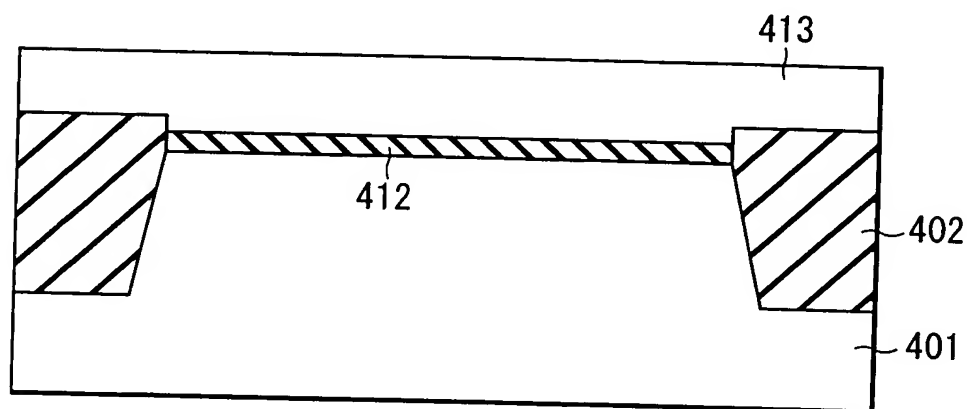


FIG. 15B

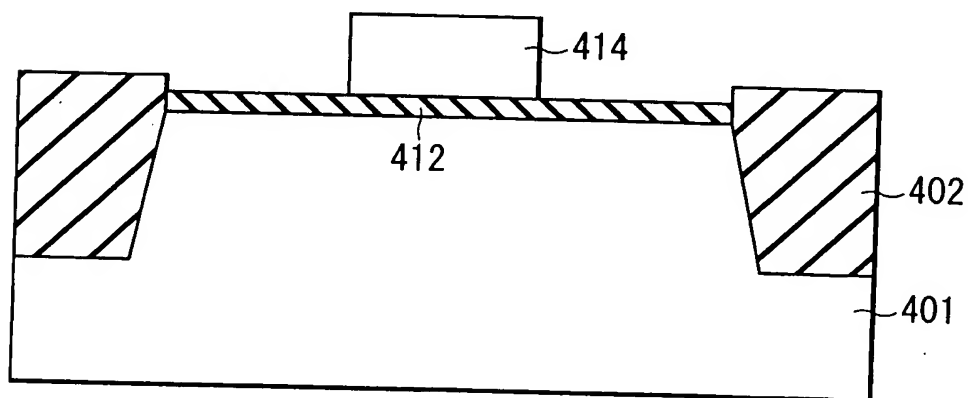


FIG. 15C

FIG. 16A

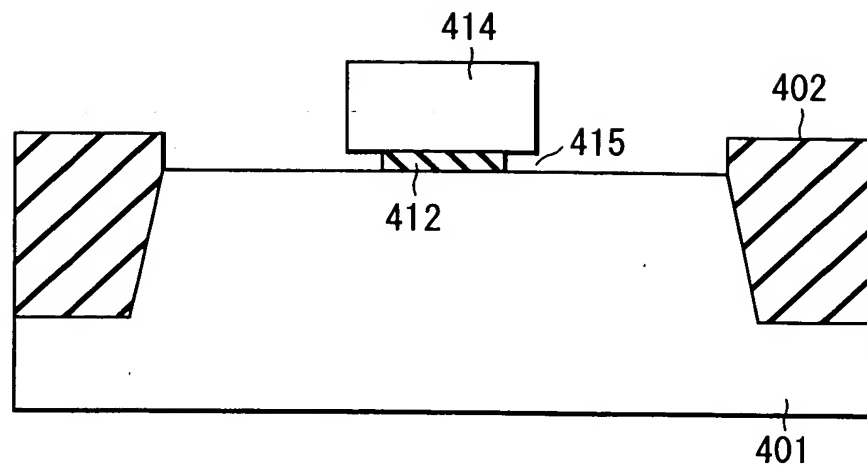


FIG. 16B

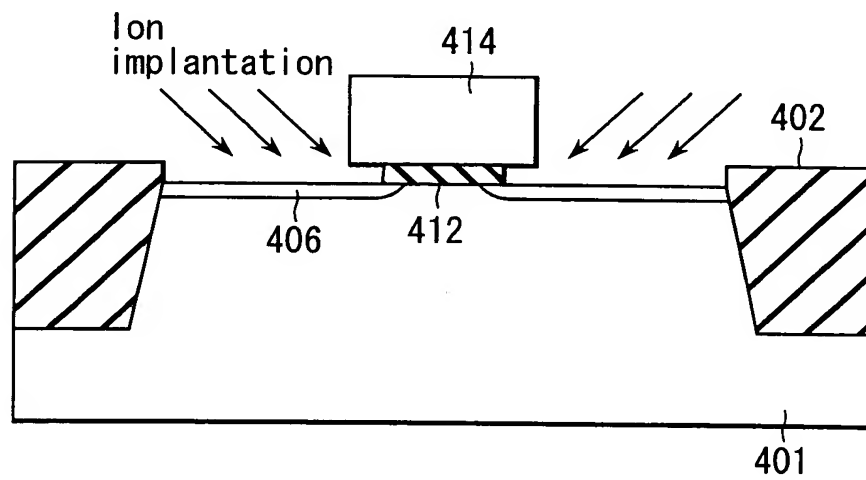


FIG. 16C

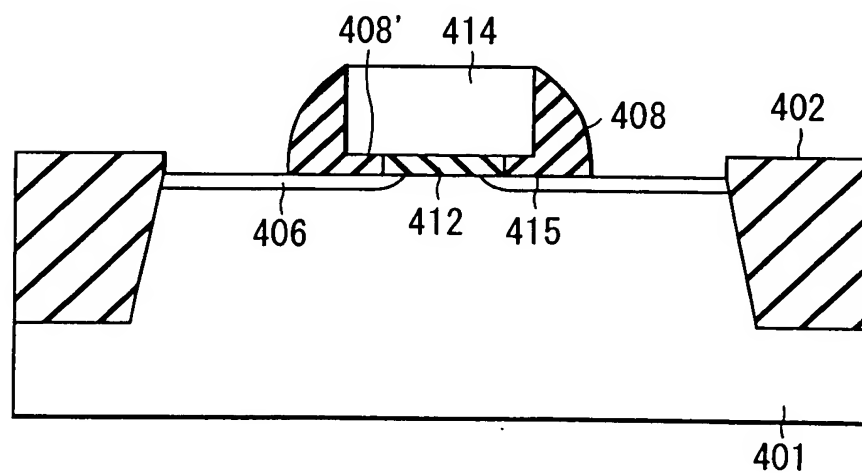


FIG. 17A

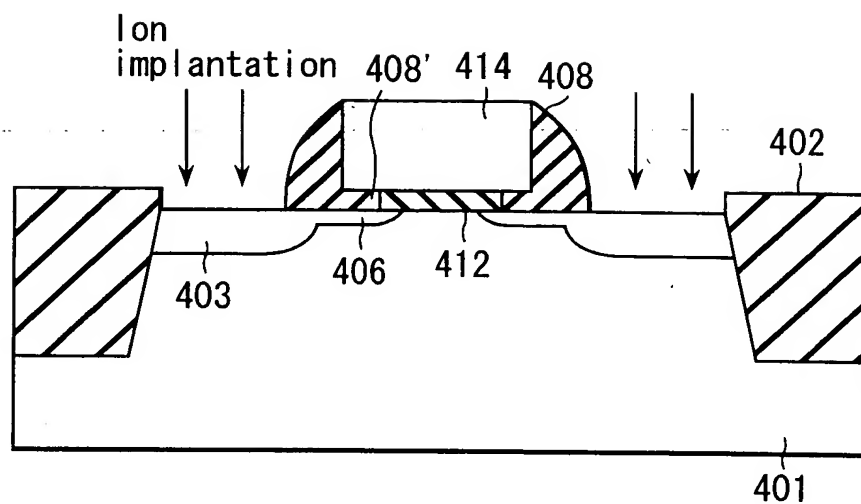


FIG. 17B

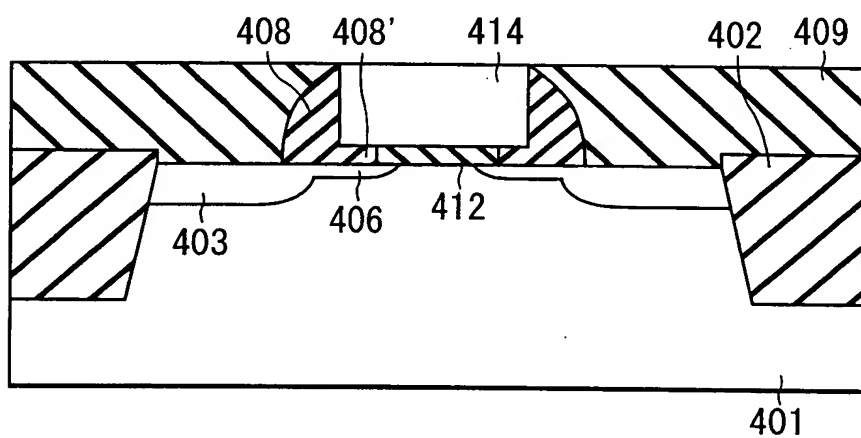
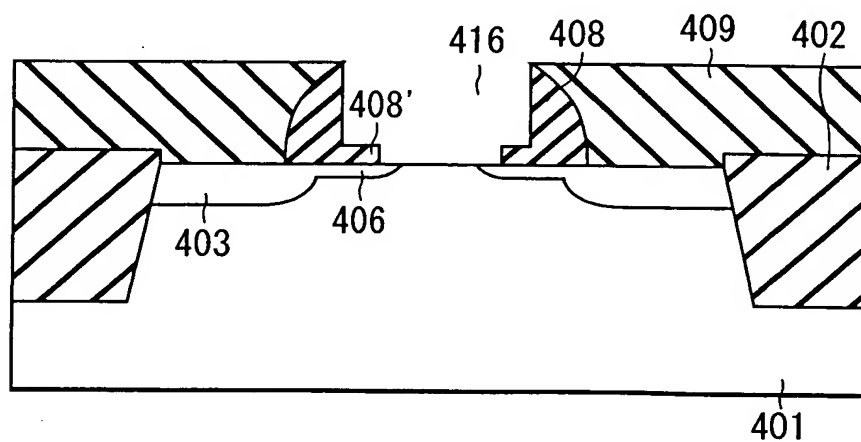


FIG. 17C



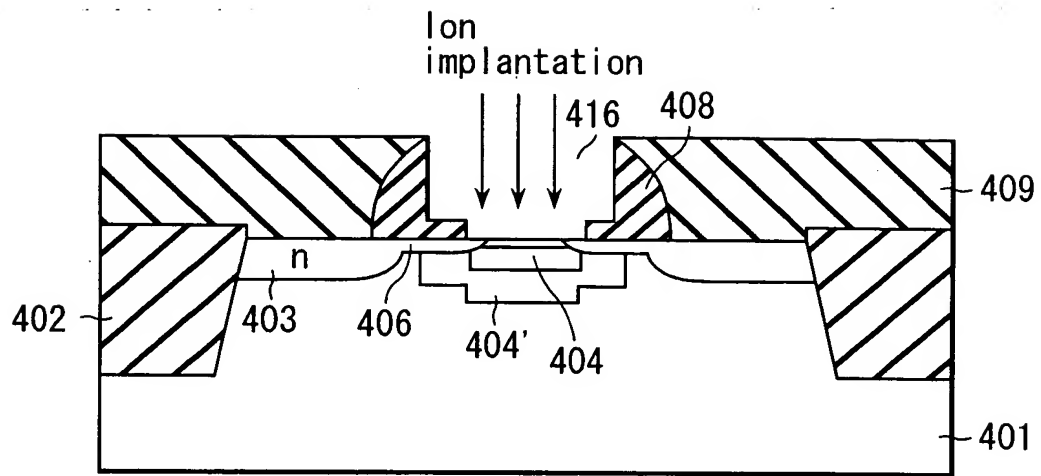


FIG. 18A

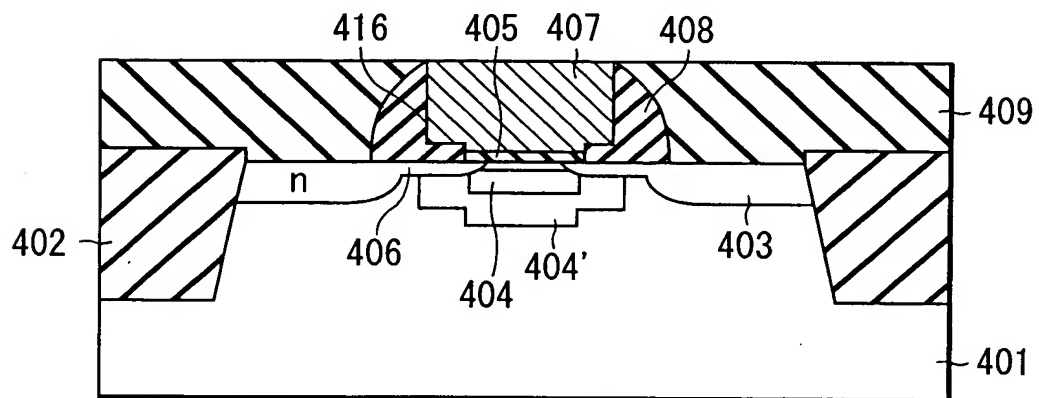


FIG. 18B

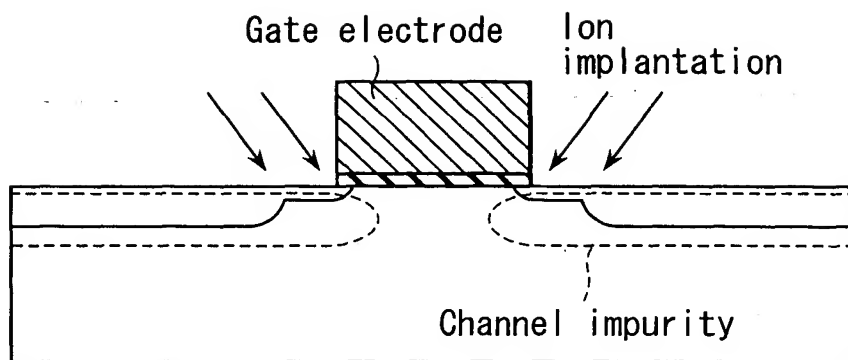


FIG. 19A PRIOR ART

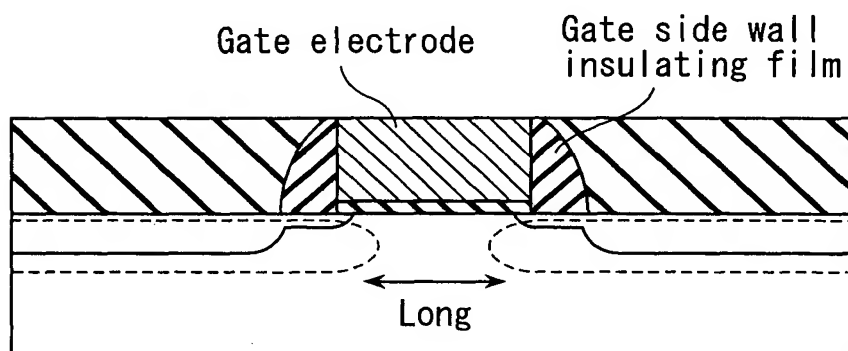


FIG. 19B PRIOR ART

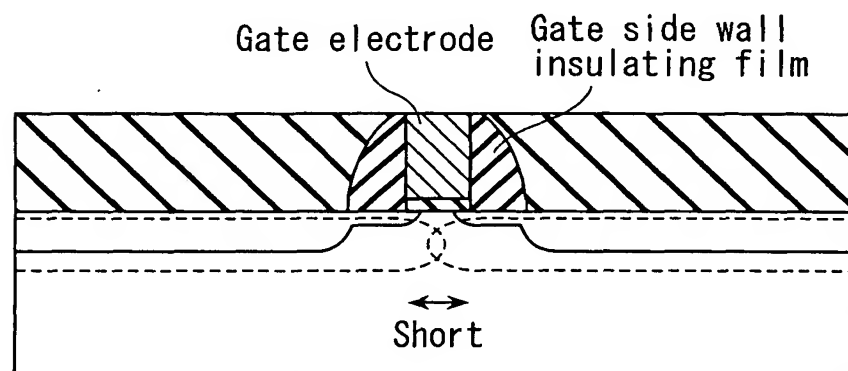


FIG. 19C PRIOR ART